

SKM 500GA123D



SEMITRANS™4

IGBT Modules

SKM 500GA123D

SKM 500GA123DS

Features

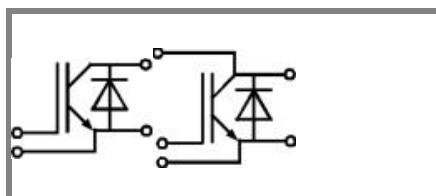
- MOS input (voltage controlled)
- N channel, homogeneous Si
- Low inductance case
- Very low tail current with low temperature dependence
- High short circuit capability, self limiting to $6 \times I_{Cnom}$
- Latch-up free
- Fast & soft CAL diodes
- Isolated copper baseplate using DBC Direct Copper Bonding Technology
- Large clearance (12 mm) and creepage distances (20 mm)

Typical Applications

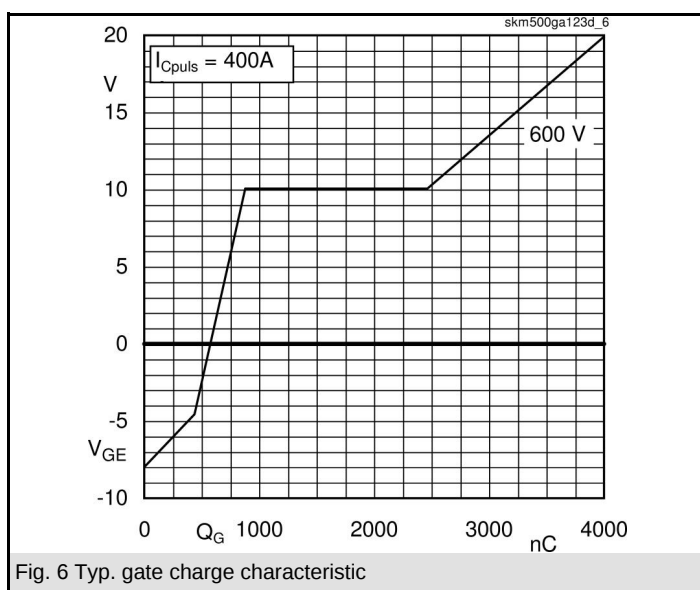
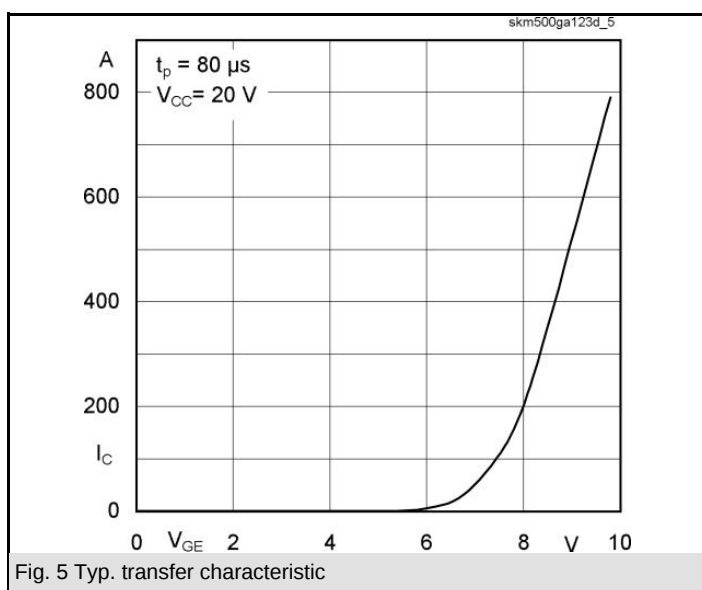
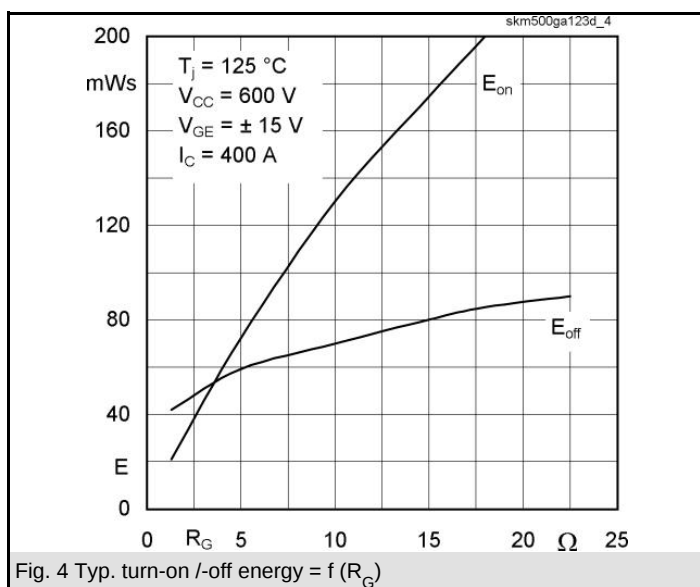
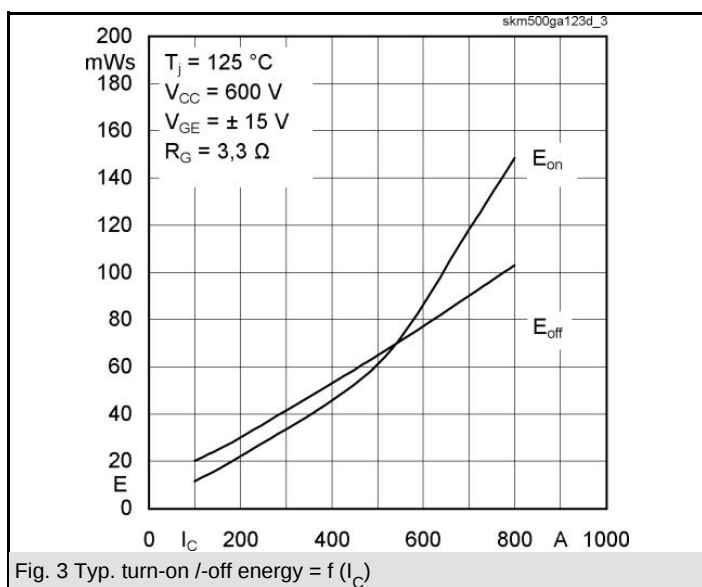
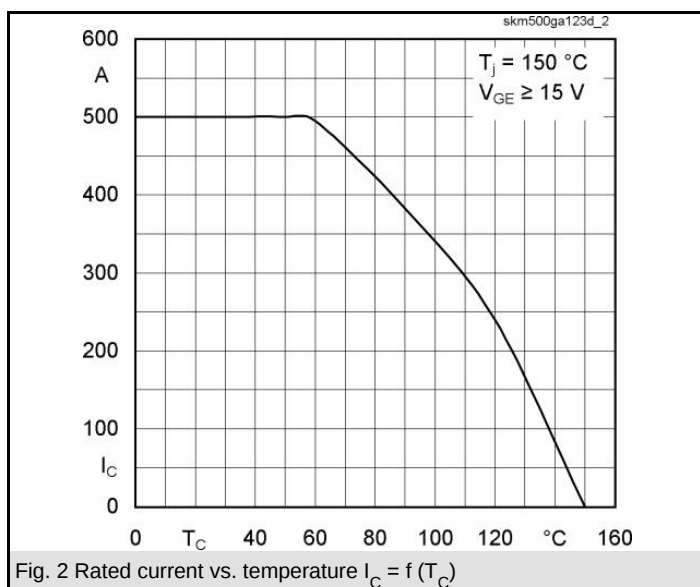
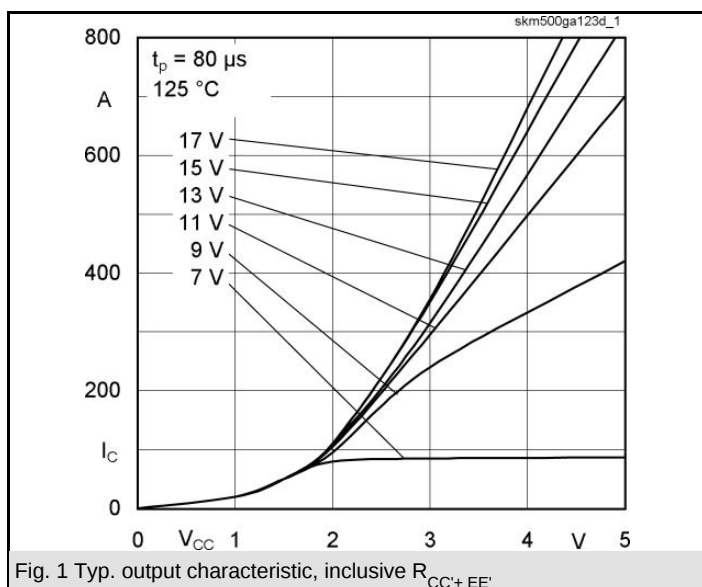
- Switching (not for linear use)

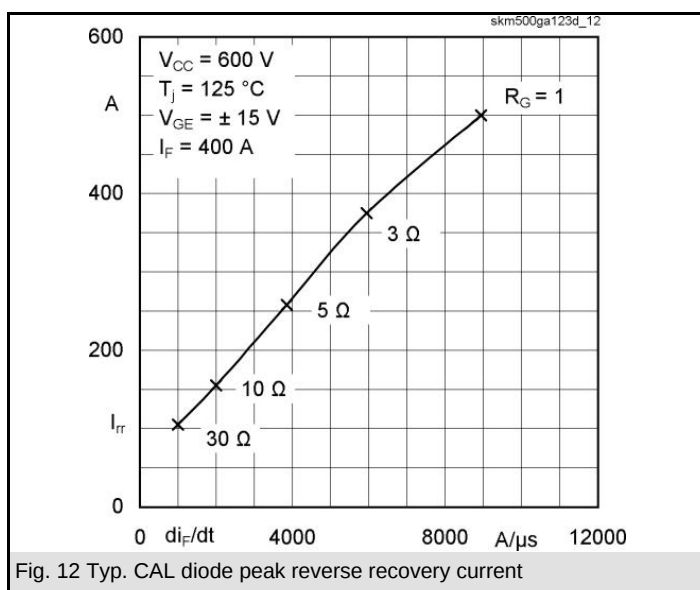
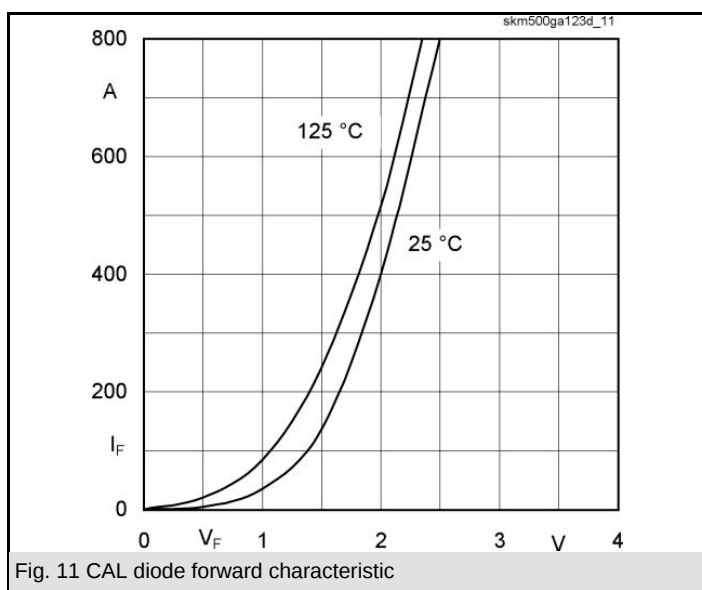
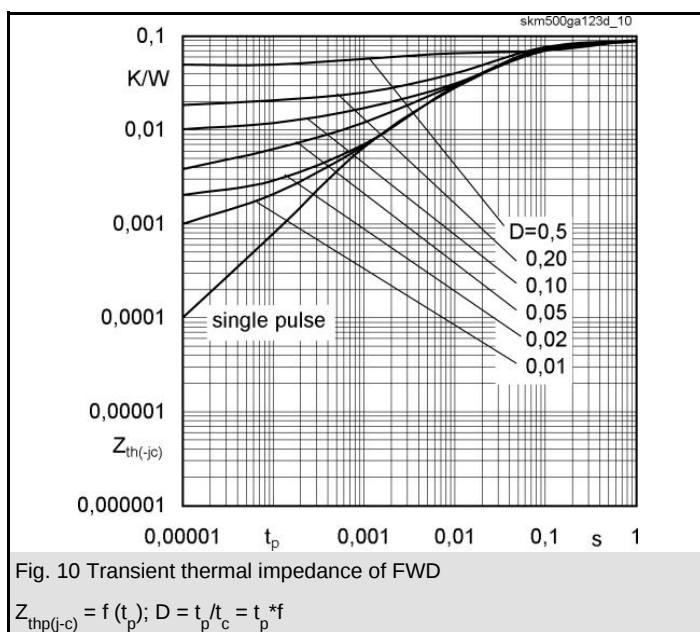
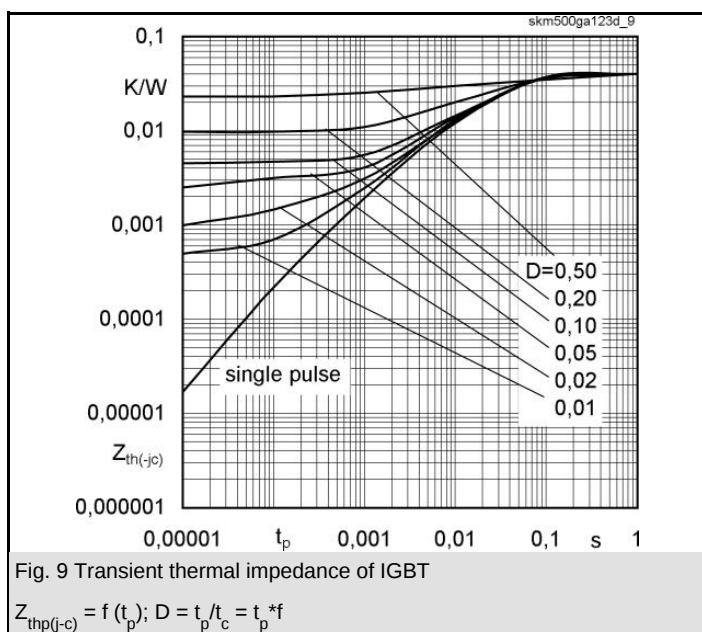
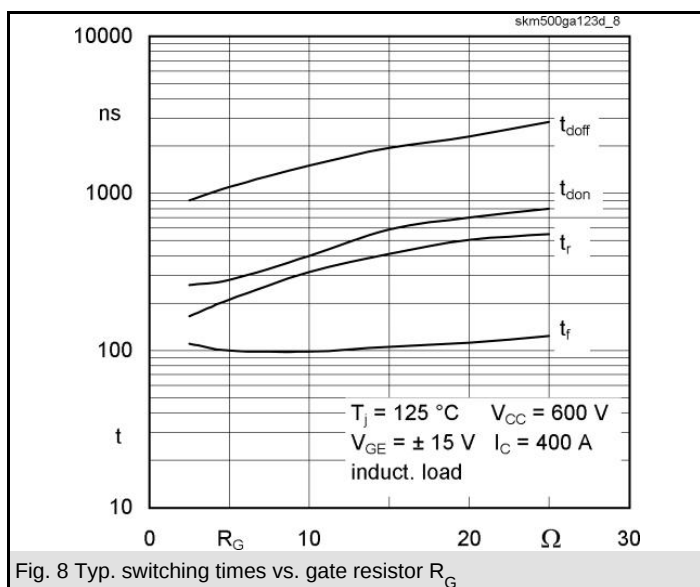
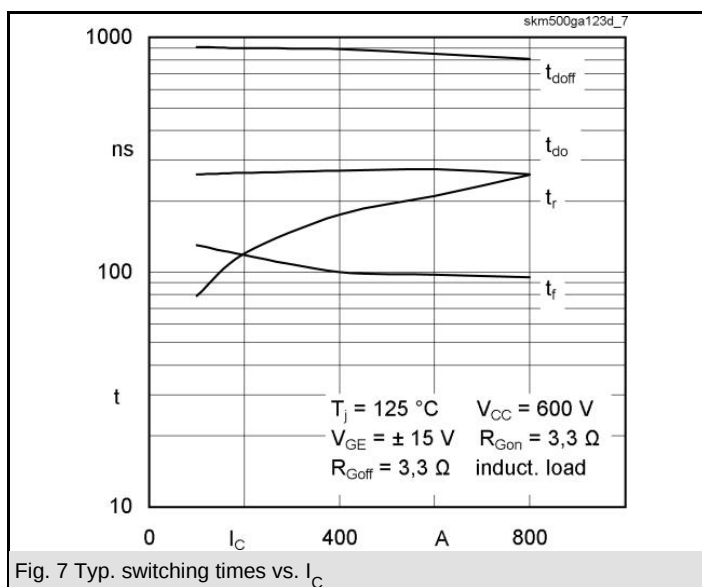
Absolute Maximum Ratings		$T_c = 25^\circ\text{C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT			
V_{CES}		1200	V
I_C	$T_c = 25 (80)^\circ\text{C}$	500 (420)	A
I_{CRM}	$t_p = 1 \text{ ms}$	800	A
V_{GES}		± 20	V
T_{vj} (T_{stg})	$T_{OPERATION} \leq T_{stg}$	- 40 ... + 150 (125)	$^\circ\text{C}$
V_{isol}	AC, 1 min.	2500	V
Inverse diode			
I_F	$T_c = 25 (80)^\circ\text{C}$	500 (350)	A
I_{FRM}	$t_p = 1 \text{ ms}$	800	A
I_{FSM}	$t_p = 10 \text{ ms}$; sin.; $T_j = 150^\circ\text{C}$	3600	A

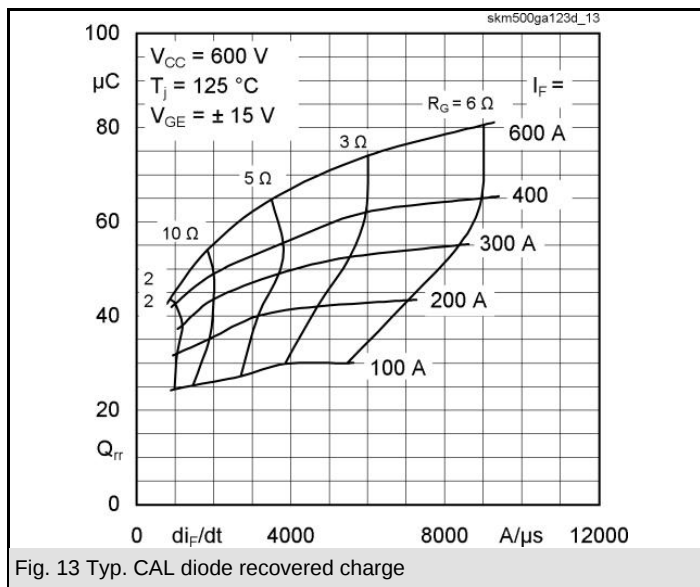
Characteristics		$T_c = 25^\circ\text{C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 16 \text{ mA}$	4,5	5,5	6,5	V
I_{CES}	$V_{GE} = 0$, $V_{CE} = V_{CES}$, $T_j = 25 (125)^\circ\text{C}$		0,1	0,3	mA
$V_{CE(TO)}$	$T_j = 25 (125)^\circ\text{C}$		1,4 (1,6)	1,6 (1,8)	V
r_{CE}	$V_{GE} = 15 \text{ V}$, $T_j = 25 (125)^\circ\text{C}$		2,75 (3,75)	3,5 (4,75)	m Ω
$V_{CE(sat)}$	$I_{Cnom} = 400 \text{ A}$, $V_{GE} = 15 \text{ V}$, chip level		2,5 (3,1)	3 (3,7)	V
C_{ies}	under following conditions		26	40	nF
C_{oes}	$V_{GE} = 0$, $V_{CE} = 25 \text{ V}$, $f = 1 \text{ MHz}$		4	5,2	nF
C_{res}			2	2,6	nF
L_{CE}				20	nH
$R_{CC'+EE'}$	res., terminal-chip $T_c = 25 (125)^\circ\text{C}$		0,18 (0,22)		m Ω
$t_{d(on)}$	$V_{CC} = 600 \text{ V}$, $I_{Cnom} = 400 \text{ A}$		250	600	ns
t_r	$R_{Gon} = R_{Goff} = 3,3 \Omega$, $T_j = 125^\circ\text{C}$		170	340	ns
$t_{d(off)}$	$V_{GE} = \pm 15 \text{ V}$		900	1100	ns
t_f			100	125	ns
$E_{on} (E_{off})$			45 (53)		mJ
Inverse diode					
$V_F = V_{EC}$	$I_{Fnom} = 400 \text{ A}$; $V_{GE} = 0 \text{ V}$; $T_j = 25 (125)^\circ\text{C}$		2 (1,8)	2,5	V
$V_{(TO)}$	$T_j = 125 ()^\circ\text{C}$			1,2	V
r_T	$T_j = 125 ()^\circ\text{C}$		1,5	3	m Ω
I_{RRM}	$I_{Fnom} = 400 \text{ A}$; $T_j = 25 (125)^\circ\text{C}$		90 (160)		A
Q_{rr}	$di/dt = 2000 \text{ A}/\mu\text{s}$		15 (50)		μC
E_{rr}	$V_{GE} = V$				mJ
Thermal characteristics					
$R_{th(j-c)}$	per IGBT			0,041	K/W
$R_{th(j-c)D}$	per Inverse Diode			0,09	K/W
$R_{th(c-s)}$	per module			0,038	K/W
Mechanical data					
M_s	to heatsink M6	3		5	Nm
M_t	to terminals M6, M4				Nm
w				330	g



GA GA...S

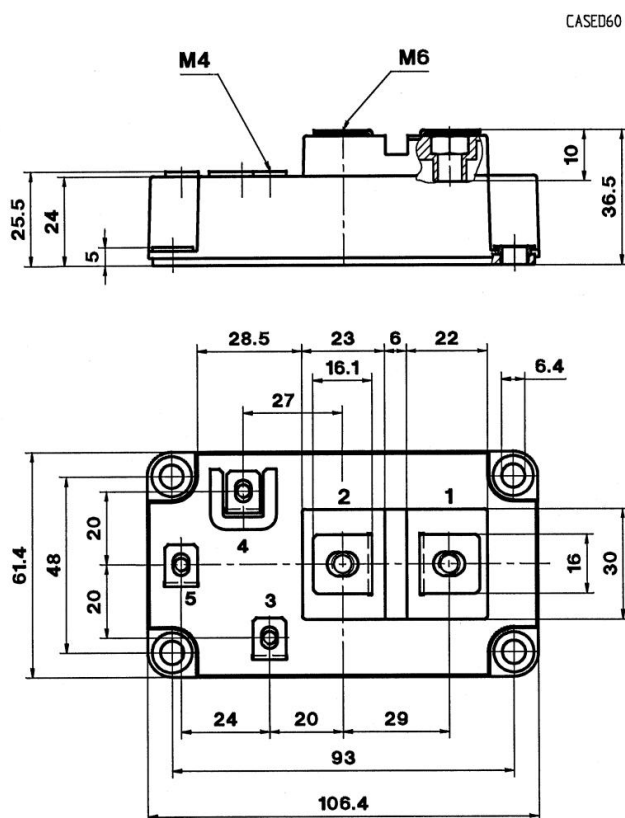




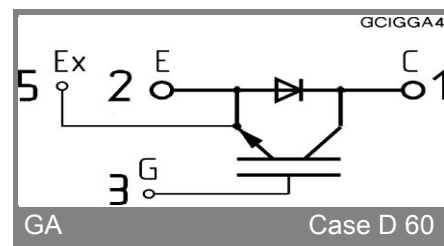


UL Recognized
File no. E 63 532

Dimensions in mm



Case D 60



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.